

Local structure analysis of Ga₂O₃ polymorphs by XAFSSatoru Yoshioka^{1,*}, Naohiro Ueno¹, Toshihiro Okajima² and Kazuhiro Hara¹¹Faculty of Engineering, Kyushu University, Fukuoka 802-3488, Japan²SAGA-LS, Saga 841-0005, Japan

1 Introduction

Gallium oxide (Ga₂O₃) has many of functionalities, such as wide-gap semiconductor for transparent conductive thin film and catalysis for dehydrogenation of paraffin to olefin. Ga₂O₃ appears a polymorphism similar to aluminum oxide. Roy *et al.* reported five polymorphs of Ga₂O₃¹. Among them, β phase which has a monoclinic structure is commonly formed under ordinary conditions. We have already reported the stability of these five phases by first principles lattice dynamics calculations². Recently, many works related to metastable phases of Ga₂O₃ were reported through chemical or physical deposition and sol-gel routes. In this study, we prepare Ga₂O₃ polymorphs by sol-gel method and investigate the local structure of them by XAFS.

2 Experiment

A total amount of 1 g gallium nitrate hydrate was solved in 50 ml water. A aqueous ammonia solution which was diluted in water (50 vol.%), was slowly added to this solution until no further precipitate was observed. The resulting gels were separated from the solutions with filter papers and were immediately washed with water. The obtained solids were calcined on a platinum foil in electric furnace at each temperature, 500, 600 and 700 °C for 1 hour. Ceramic specimens were powdered before structure analysis.

Ga K-edge XAFS spectra were obtained at BL-7C of Photon Factory (PF) in High Energy Accelerator Research Organization (KEK). All of the spectra were recorded in transmission mode at room temperature with Si(111) double crystal monochromator. Specimens are diluted by high purity hexagonal type boron nitride powder before measurement.

3 Results and Discussion

The XRD measurements of samples were performed with versatile Cu-tube type instruments. The diffraction patterns of the sample calcined at 500 °C and 700 °C are indexed as α -Ga₂O₃ with corundum structure and β -Ga₂O₃, respectively. The profile of the sample calcined at 600 °C is mixed with α -Ga₂O₃ and β -Ga₂O₃. Ga K-edge XANES spectra of these samples are showed in Fig. 1, together with standard sample of β -Ga₂O₃. The spectrum of α -Ga₂O₃ (calcined at 500 °C) shows single peak at 10376 eV. Alpha phase of Ga₂O₃ has only one Ga site, which is octahedral. On the other hands, β -Ga₂O₃ spectrum has a peak with a shoulder at which is located at 10372 eV (indicated with an arrow in Fig. 1). Beta phase has equal numbers of two kind Ga sites, tetrahedral and

octahedral ones. Theoretical XANES spectrum of β -Ga₂O₃ performed by first principles calculation shows that the rising edge of spectra is mainly composed by tetrahedral site and strong main peak is composed by octahedral site³. In comparison to the standard sample β -Ga₂O₃, the ration of intensity between the main peak and shoulder in the spectra of the sample calcinated at 700 °C which is assigned as β phase by XRD, is slightly different. It shows that atom arrangement in long range is composed, but local structure is not conclusively laid out as β -Ga₂O₃.

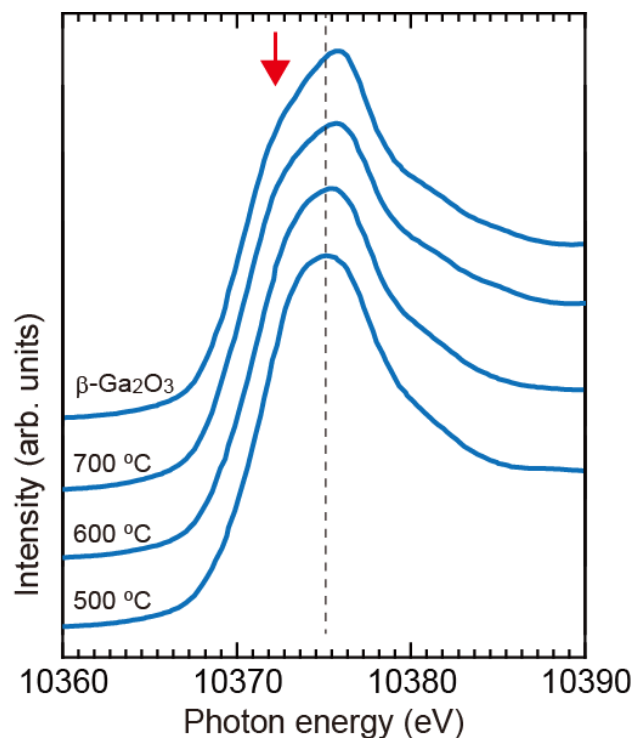


Fig. 1: Ga K-edge XANES spectra of samples prepared with water and calcined at each temperature for 1 h, together with that of β -Ga₂O₃ as a reference.

References

- [1] R. Roy *et al.*, J. Chem. Soc. 74 [3], 719-22 (1952)
- [2] S. Yoshioka *et al.*, J. Phys.: Cond. Mat. 19, 346211 (2007)
- [3] I. Tanaka *et al.*, Nature Mat. 2, 541-545 (2003)

* syoshioka@nucl.kyushu-u.ac.jp